

Title (en)

A DMOS DEVICE WITH A PROGRAMMABLE THRESHOLD VOLTAGE

Title (de)

DMOS-BAUELEMENT MIT PROGRAMMIERBARER SCHWELLENSPANNUNG

Title (fr)

DISPOSITIF MOS A DOUBLE DIFFUSION A TENSION DE SEUIL PROGRAMMABLE

Publication

EP 1550150 A2 20050706 (EN)

Application

EP 03751848 A 20030811

Priority

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Abstract (en)

[origin: WO2004015745A2] A DMOS device is provided which is equipped with a floating gate having a first and second electrode in close proximity thereto. The floating gate is separated from one of the first and second electrodes by a thin layer of dielectric material whose dimensions and composition permit charge carriers to tunnel through the dielectric layer either to or from the floating gate. This tunneling phenomenon can be used to create a threshold voltage that may be adjusted to provide a precise current by placing a voltage between a programming electrode and the body/source and gate electrode of the device.

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G11C 16/04

IPC 8 full level

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